BCX79





PNP General Purpose Amplifier

This device is designed for use as general purpose amplifiers and switches requiring collector currents to 300 mA. Sourced from Process 68. See PN200A for characteristics.

Absolute Maximum Ratings* TA = 25°C unless otherwise noted

Symbol	Parameter	Value	Units
V _{CEO}	Collector-Emitter Voltage	45	V
V _{CES}	Collector-Base Voltage	45	V
V _{EBO}	Emitter-Base Voltage	5.0	V
I _C	Collector Current - Continuous	500	mA
T _J , T _{stg}	Operating and Storage Junction Temperature Range	-55 to +150	°C

*These ratings are limiting values above which the serviceability of any semiconductor device may be impaired.

NOTES:

1) These ratings are based on a maximum junction temperature of 150 degrees C.
 2) These are steady state limits. The factory should be consulted on applications involving pulsed or low duty cycle operations.

Thermal Characteristics

Thermal Characteristics TA = 25°C unless otherwise noted				
Symbol	Characteristic	Max	Units	
		BCX79	1	
PD	Total Device Dissipation	625	mW	
	Derate above 25°C	5.0	mW/°C	
$R_{\theta JC}$	Thermal Resistance, Junction to Case	83.3	°C/W	
$R_{ extsf{ heta}JA}$	Thermal Resistance, Junction to Ambient	200	°C/W	

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PNP General Purpose Amplifier (continued)

Symbol	Parameter	Test Conditions	Min	Мах	Units
OFF CHA	RACTERISTICS				
V _{(BR)CEO}	Collector-Emitter Breakdown Voltage	$I_{\rm C} = 10 \text{ mA}, I_{\rm B} = 0$	45		V
V _{(BR)EBO}	Emitter-Base Breakdown Voltage	$I_E = 1.0 \ \mu A, \ I_C = 0$	5.0		V
I _{CEX}	Collector Cutoff Current	$V_{CE} = 45 \text{ V}, V_{BE} = 0.2 \text{ V},$ $T_A = +100 ^{\circ}\text{C}$		20	μΑ
I _{CES}	Collector Cutoff Current	$ \begin{array}{l} V_{CE} = 45 \; V, \; I_E = 0, \\ V_{CE} = 45 \; V, \; I_E = 0, \; T_A = +125 \; ^{\circ}C \\ V_{EB} = 4.0 \; V, \; I_C = 0 \end{array} $		10 2.5	nA μA
I _{EBO}	Emitter Cutoff Current	$V_{EB} = 4.0 \text{ V}, I_{C} = 0$		20	nA
ON CHAR	ACTERISTICS				
h _{FE}	DC Current Gain		120 80 40	630 1,000	
V _{CE(sat)}	Collector-Emitter Saturation Voltage	$V_{CE} = 1.0 \text{ v}, \text{ I}_{C} = 100 \text{ mA}$ $I_{C} = 100 \text{ mA}, \text{ I}_{B} = 2.5 \text{ mA}$	UT	0.6	V
V _{BE(sat)}	Base-Emitter Saturation Voltage	$I_{\rm C} = 100$ mA, $I_{\rm B} = 2.5$ mA		1.0	V
V _{BE(On)}	Base-Emitter On Voltage	$V_{CE} = 5.0 \text{ V}, I_{C} = 2.0 \text{ mA}$	0.6	0.7	V
52(01)	_	$V_{CE} = 1.0 \text{ V}, I_{C} = 100 \text{ mA}$		0.9	V
SMALL S	IGNAL CHARACTERISTICS			1.15	
2					
	Collector-Base Capacitance	$V_{CB} = 10 \text{ V}, \text{ f} = 1.0 \text{ MHz}$		4.5	pF
C _{eb}	Emitter-Base Capacitance	V _{EB} = 0.5 V, f = 1.0 MHz		15	pF
C _{eb} h _{ie}	Emitter-Base Capacitance Input Impedance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$	1.6	15 8.5	pF kΩ
C _{eb} h _{ie}	Emitter-Base Capacitance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ f = 1.0 kHz $I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$	1.6	15	pF kΩ
C _{eb} h _{ie} h _{oe}	Emitter-Base Capacitance Input Impedance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, f = 1.0 \text{ kHz}$	1.6	15 8.5	pF kΩ
C _{eb} h _{ie} h _{oe}	Emitter-Base Capacitance Input Impedance Output Admittance	$V_{EB} = 0.5 \text{ V}, f = 1.0 \text{ MHz}$ $I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$ $I_{C} = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V},$ $f = 1.0 \text{ kHz}$	1.6	15 8.5 100	pF kΩ μmhos
C _{eb} h _{ie} h _{oe} NF	Emitter-Base Capacitance Input Impedance Output Admittance	$\begin{split} V_{EB} &= 0.5 \text{ V}, \text{ f} = 1.0 \text{ MHz} \\ I_{C} &= 2.0 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ \text{f} &= 1.0 \text{ kHz} \\ I_{C} &= 2.0 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ \text{f} &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} = 0.2 \text{ mA}, \end{split}$	1.6	15 8.5 100	pF kΩ μmhos
C _{eb} h _{ie} NF SWITCHII	Emitter-Base Capacitance Input Impedance Output Admittance Noise Figure	$\begin{split} V_{EB} &= 0.5 \text{ V}, \text{ f} = 1.0 \text{ MHz} \\ I_{C} &= 2.0 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ \text{f} &= 1.0 \text{ kHz} \\ I_{C} &= 2.0 \text{ mA}, \text{ V}_{CE} = 5.0 \text{ V}, \\ \text{f} &= 1.0 \text{ kHz} \\ V_{CE} &= 5.0 \text{ V}, \text{ I}_{C} &= 0.2 \text{ mA}, \\ \text{R}_{S} &= 2.0 \text{ k}\Omega, \text{ f} &= 1.0 \text{ kHz} \\ \end{split}$	1.6	15 8.5 100	pF kΩ μmhos
C _{eb} h _{ie} h _{oe} NF SWITCHI	Emitter-Base Capacitance Input Impedance Output Admittance Noise Figure NG CHARACTERISTICS Turn-on Time	$\begin{split} & V_{EB} = 0.5 \text{ V}, \text{ f} = 1.0 \text{ MHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & V_{CE} = 5.0 \text{ V}, I_C = 0.2 \text{ mA}, \\ & R_S = 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz} \\ \end{split}$	1.6	15 8.5 100 6.0 150	pF kΩ μmhos dB
C _{eb} h _{ie} NF SWITCHII	Emitter-Base Capacitance Input Impedance Output Admittance Noise Figure	$\begin{split} & V_{EB} = 0.5 \text{ V}, \text{ f} = 1.0 \text{ MHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & V_{CE} = 5.0 \text{ V}, I_C = 0.2 \text{ mA}, \\ & R_S = 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz} \\ \end{split}$	1.6	15 8.5 100 6.0	pF kΩ μmhos dB
C _{cb} C _{eb} h _{ie} h _{oe} NF SWITCHII t _{on} t _{on} t _{onf}	Emitter-Base Capacitance Input Impedance Output Admittance Noise Figure NG CHARACTERISTICS Turn-on Time	$\begin{split} & V_{EB} = 0.5 \text{ V}, \text{ f} = 1.0 \text{ MHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & V_{CE} = 5.0 \text{ V}, I_C = 0.2 \text{ mA}, \\ & R_S = 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz} \\ \end{split}$	1.6	15 8.5 100 6.0 150	pF kΩ μmhos dB
C _{eb} h _{ie} h _{oe} NF SWITCHII	Emitter-Base Capacitance Input Impedance Output Admittance Noise Figure NG CHARACTERISTICS Turn-on Time Turn-on Time	$\begin{split} & V_{EB} = 0.5 \text{ V}, \text{ f} = 1.0 \text{ MHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & I_C = 2.0 \text{ mA}, V_{CE} = 5.0 \text{ V}, \\ & f = 1.0 \text{ kHz} \\ & V_{CE} = 5.0 \text{ V}, I_C = 0.2 \text{ mA}, \\ & R_S = 2.0 \text{ k}\Omega, \text{ f} = 1.0 \text{ kHz} \\ \end{split}$	1.6	15 8.5 100 6.0 150 150	pF kΩ μmhos dB ns ns

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